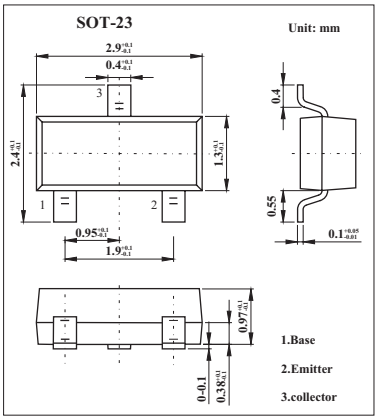
Silicon PNP Epitaxial

2SA1617

■ Features



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-55	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = -10μA , I_E = 0	-55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1mA , R_{BE} = ∞	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = -10μA , I_C = 0	-5			V
Collector cutoff current	I_{CBO}	V_{CB} = -30V, I_E=0			-0.5	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -2V, I_C=0			-0.5	μA
DC current gain	h_{FE}	V_{CE} = -12V , I_C = -2mA	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -10mA , I_B = -1mA			-0.2	V
Base-emitter voltage	V_{BE}	V_{CE} = -12V , I_C = -2mA			-0.8	V

■ h_{FE} Classification

Marking	VI	
Rank	B	C
hFE	100～200	160～320